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PATENT Attorney Docket No.: 000939-045100US

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Hsingya Arthur Wang, et al.

Application No.: 09/777,007

Filed: February 2, 2001

For: SOURCE SIDE PROGRAMMING

Kiesha L. Rose Examiner: TECHNOLOGY CENTER 2800 Art Unit: **AMENDMENT** 

Assistant Commissioner for Patents Washington, D.C. 20231

In response to the Office Action mailed August 30, 2002, please amend Sir: the above-identified application as follows:

## IN THE SPECIFICATION:

On page 1, please replace the sixth paragraph with the following

paragraph:

-- FIG. 1 shows a cell 10 with a control gate 12, a floating gate 14, a

source 16 and a drain 18. Control gate 12 and floating gate 14 are separated from source 16 and drain 18, and from a substrate 11 into which the source 16 and drain 18 are formed, by an oxide 22 which may be formed by one or more layers of a suitable oxide material. Suitable openings in the oxide 22 are provided to allow for external connection to source 16 and drain 18. As shown, connections are provided to set V<sub>8</sub> (control gate voltage),  $V_d$  (drain voltage),  $V_s$  (source voltage) and  $V_b$  (substrate voltage). --